HII	Search Text	DBs	Time 8
1 1	"20020074583"	USPAT; US-PGPUB	2002/12
2 1	*20020074583* and force	USPAT; US-PGPUB	2002/12
3 12	(((non\$1volatile with (semiconductor or memory)) or eprom or eeprom or flash).ab.) and ((lightly adj doped) adj drain) and (floatin	USPAT; US-PGPUB	2002/12
4 4		USPAT; US-PGPUB	2002/12
5 2	*6297098 <b>*</b>	USPAT; US-PGPUB	2002/12
6 1		USPAT	2002/12
7 15	(((non\$1volatile with (semiconductor or memory)) or eprom or eeprom or flash).ab.) and (((lightly adj doped) adj drain) with (belo	USPAT; US-PGPUB	2002/12
8 0	(((non\$1volatile with (semiconductor or memory)) or eprom or eeprom or flash) and (floating adj gate) and ("not" adj (surfac		2002/12
	(((non\$1volatile with (semiconductor or memory)) or eprom or eeprom or flash).ab.) and (floating adj gate) and ((257/221.ccls.)		2002/12
10 0	(((non\$1volatile with (semiconductor or memory)) or eprom or eeprom or flash).ab.) and (floating adj gate) and ((257/221.ccls.)	USPAT; US-PGPUB	2002/12
11 5		USPAT; US-PGPUB	2002/12
		USPAT; US-PGPUB	2002/12
		USPAT; US-PGPUB	2002/12
	(((non\$1volatile with (semiconductor or memory)) or eprom or eeprom or flash).ab.) and (floating adj gate) and ((257/221.ccls.)		2002/12
15 11			2002/12
16 0	(((non\$1volatile with (semiconductor or memory)) or eprom or eeprom or flash).ab.) and ((increase or increased or increasing) wi		2002/12
17 1	(((non\$1volatile with (semiconductor or memory)) or eprom or eeprom or flash).ab.) and ((increase or increased or increasing) wi		2002/12
		USPAT; US-PGPUB	2002/12
19 1		USPAT; US-PGPUB	2002/12
20 1		USPAT	2002/12
21 1		USPAT	2002/12
22 1		USPAT	2002/12
23 1		USPAT	2002/12
24 1		USPAT	2002/12
25 1	$\phi(a) = 0$	USPAT	2002/12
26 1		USPAT	2002/12
27 5	*5912487*	USPAT; US-PGPUB	2002/12
28 7	(((non\$1 volatile with (semiconductor or memory)) or eprom or eeprom or flash) with asymmetric) and ((257/221.ccls.) or (257/2		2002/12
		USPAT; US-PGPUB	2002/12
30 5	(((non\$1volatile with (semiconductor or memory)) or eprom or eeprom or flash) ab.) and ((embedded or buried) adj (Idd or (lighti		2002/12
31 7	((non\$1volatile or eprom or eeprom or flash) with asymmetric) and ((257/221.ccls.) or (257/285.ccls.) or (257/403.ccls.) or (25		2002/12
	((non\$1volatile or eprom or eeprom or flash or (floating adj gate)).ab.) and ((protruding or protrude or extend or extending or ext		2002/12
33 0	((non\$1volatile or eprom or eeprom or flash or (floating adj gate) ).ab.) and ((Idd or ((lightly\$1doped or (lightly adj doped)) adj dra		2002/12
34 0 35 9	((non\$1volatile or eprom or eeprom or flash or (floating adj gate) ).ab.) and ((stick or sticking) adj (fldd or (flightly\$1 doped or (flightly\$1)).ab.)		2002/12 2002/12
	((non\$1volatile with (semiconductor or memory)) or eprom or eeprom or flash).ab.) and ((increase or increased or increasing) wi ((non\$1volatile or eprom or eeprom or flash or (floating adj gate) ).ab.) and ((protruding or protrude or extend or extending or ex		2002/12
37 7	((non\$1volatile or eprom or eeprom or flash or (floating adj gate) ).ab.) and ((protruding or protrude or extend or extending or extend		2002/12
38 2	((non\$1volatile or eprom or eeprom or flash)) and ((buried or embedded) with halo) and ((257/\$.ccls) or (438/\$.ccls.) or (365/\$.		2002/12
39 I	((non\$1volatile or eprom or eeprom or flash)) and (left with drain with halo) and ((257/\$.ccls) or (438/\$.ccls.) or (365/\$.ccls.))		2002/12
40 o	((non\$1volatile or eprom or eeprom or flash)) and (halo with ((beneath or under or below) adj drain)) and ((257/\$.ccis.) or (438/\$.ccis.)		2002/12
41 1	((non\$ volatile or eprom or eeprom or flash)) and (halo with ((beneath or under or below) adj channel)) and ((2575.ccts) or (43		2002/12
42 1	((non\$1volatile or eprom or eeprom or flash)) and (pocket with ((beneath or under or below) adj channel)) and ((257/\$.ccls) or (		2002/12
43 5	((nons totalile or eprom or eeprom or flash or (floating adjate)).eb.and ((protuding or protude or extend or extending or ext		2002/12
77 h		HISDAT-HIS DODHR	2002/12
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45 0 ((r 46 1 "5 47 1 "5 49 1 "5 50 1 "5 51 1 "5 52 1 "5 63 1 "5	non\$1volatile or eprom or eeprom or flash or (floating adj gate) )) and (5270226.PN. and (*4680603")) 5721442".PN. 5721442".PN. 5780341".PN. 5337274".PN. 541428".PN. 5414287".PN. 5656839".PN. 5656839".PN.	USPAT; US-PGPUB USPAT; US-PGPUB USPAT USPAT USPAT USPAT USPAT USPAT USPAT USPAT	2002/12/0 2002/12/0 2002/12/0 2002/12/0 2002/12/0 2002/12/0 2002/12/0
46 1 "5 47 1 "5 48 1 "5 49 1 "5 50 1 "5 51 1 "5 52 1 "5 63 1 "5	5721442*PN. 5721442*PN. 5780341*PN. 5337274*PN. 6414287*PN. 6656839*PN. 5719425*PN.	USPAT USPAT USPAT USPAT USPAT USPAT	2002/12/0 2002/12/0 2002/12/0 2002/12/0 2002/12/0
47 1 '5 48 1 '5 49 1 '5 50 1 '5 51 1 '5 52 1 '5 53 1 '5	721442*PN. 5780341*PN. 3337274*PN. 5414287*PN. 5656839*PN. 5719425*PN.	USPAT USPAT USPAT USPAT USPAT USPAT	2002/12/0 2002/12/0 2002/12/0 2002/12/0
48 1 *5 49 1 *5 50 1 *5 61 1 *5 52 1 *5 53 1 *5	5780341°.PN. 5337274°.PN. 5414287°.PN. 565839°.PN. 5719425°.PN.	USPAT USPAT USPAT USPAT USPAT	2002/12/0 2002/12/0 2002/12/0
49 1 5 50 1 5 61 1 5 52 1 5 53 1 5	337274".PN. 3414287".PN. 3656839".PN. 3719425".PN.	USPAT USPAT USPAT	2002/12/0 2002/12/0
50 1 5 51 1 5 52 1 5 63 1 5	414287° PN. 6556839° PN. 5719425° PN.	USPAT USPAT	2002/12/0
61 1 *5 52 1 *5 63 1 *5	656839".PN. 5719425".PN.	USPAT	
52 1 °5 53 1 °5	719425".PN.		
<b>53</b> 1 *5			2002/12/0
	0/4/849°.PN.		2002/12/0
3 <b>3104</b> 0001 5	5721442° PN.	USPAT USPAT	2002/12/0
55 1 *5		USPAT	2002/12/0
* * * * * * * * * * * * * * * * * * *	778034 I-FN. 60038881*	EPO; JPO; DERWENT; IBM	¢
		USPAT; US-PGPUB	2002/12/0
		USPAT: US-PGPUB	2002/12/0
		USPAT: US-PGPUB	2002/12/0
		USPAT	2002/12/0
		USPAT	2002/12/0
**************************************		USPAT	2002/12/0
	non\$1volatile or eprom or eeprom or flash or (floating adj gate) ).ab.) and (( halo or pocket) with ((below or beneath or under) a		2002/12/0
	non\$1volatile or eprom or eeprom or flash or (floating adj gate) ).ab.) and (((halo or pocket) adj (below or beneath or under)) w		2002/12/0
	non\$1volatile or eprom or eeprom or flash or (floating adj gate)).ab.) and ((halo or pocket) adj (below or beneath or under))		2002/12/0
	non\$1volatile or eprom or eeprom or flash or (floating adj gate) ).ab.) and ((halo or pocket) with (surface or (substrate adj surf		2002/12/0
67 1 ((r	non\$1volatile or eprom or eeprom or flash or (floating adj gate) ).ab.) and ((halo or pocket) with (middle or center) with drain)		2002/12/0
68 3 (fl	loating adj (gate or electrode)) and ((doping or impurity) adj ((beneath or below or under) adj channel))	USPAT; US-PGPUB	2002/12/0
69 8 (fl		USPAT; US-PGPUB	2002/12/0
70 3 (fl	loating adj (gate or electrode)) and (((edge) adj channel) with (n\$1type or (n adj type)))	USPAT; US-PGPUB	2002/12/0
		USPAT	2002/12/0
		USPAT	2002/12/0
**************************************	, and a second control of the contro	USPAT	2002/12/0
		USPAT	2002/12/0
**************************************		USPAT	2002/12/0
		USPAT	2002/12/0
		USPAT	2002/12/0
		USPAT USPAT	2002/12/0
		USPAT; US-PGPUB	2002/12/0
		USPAT: US-PGPUB	2002/12/0
		USPAT; US-PGPUB	2002/12/0
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Hits	Search Text		DBs	Time 5
<b>97</b> 0	(floating adj (gate or electrode)) and ((doping or impurity) adj beneath adj surface)	USPAT;	US-PGPUB	2002/12
88 26		USPAT;	US-PGPUB	2002/12
		USPAT		2002/12
90 1	*5380670*.PN.	USPAT		2002/12
91 1		USPAT		2002/12
92 1	((floating adj (gate or electrode)) and *4775642*) and ((lateral or laterally) with (diffuse or movement or diffusion or diffusing or	USPAT;	US-PGPUB	2002/12
93 15	(floating adj (gate or electrode)) and (drain with protrusion)	USPAT;	US-PGPUB	2002/12
	((floating adj (gate or electrode)) and (drain with extension)) and ((lateral or laterally) with (diffuse or movement or diffusion or dif			2002/12
95 11	(floating adj (gate or electrode)) and ((lateral or laterally) with (diffuse or movement or diffusion or diffusing or diffused or migrati	USPAT;	US-PGPUB	2002/12
96 10	((floating adj (gate or electrode)) and ((lateral or laterally) with (diffuse or movement or diffusion or diffusing or diffused or migrat	USPAT;	US-PGPUB	2002/12
97 13	(floating adj (gate or electrode)) and (drain with protruding)	USPAT;	US-PGPUB	2002/12
98 3	(floating adj (gate or electrode)) and ((lateral or laterally) with (diffuse or movement or diffusion or diffusing or diffused or migrati	USPAT;	US-PGPUB	2002/12
	(floating adj (gate or electrode)) and ((lateral or laterally) with (diffuse or movement or diffusion or diffusing or diffused or migrati			2002/12
			US-PGPUB	2002/12
101 13	(floating adj (gate or electrode)) and ( lower with corner with drain) ((floating adj (gate or electrode)) or ( (non\$1volatile or (non adj volatile)) with (memory or semiconductor))) and ( lower with cor	USPAT;	US-PGPUB	2002/12
102 4	((floating adj (gate or electrode)) or ( (non\$1volatile or (non adj volatile)) with (memory or semiconductor))) and ( lower with cor	EPO; JF	O; DERWENT; IBM_	2002/12
103 5	"5646430"	USPAT;	US-PGPUB	2002/12
104 23	*5264384*	USPAT;	US-PGPUB	2002/12
105 16	((floating adj (gate or electrode)) or ( (non\$1volatile or (non adj volatile)) with (memory or semiconductor))) and ( comer with dr			2002/12
	A100-13 - 14 - 15 - 15 - 15 - 15 - 15 - 15 - 15		US-PGPUB	2002/12
107 33	·5349225'		US-PGPUB	2002/12
	Av	***************************************	US-PGPUB	2002/12
	$X_1 \dots X_{n-1} $		US-PGPUB	2002/12
			US-PGPUB	2002/12
111 7			US-PGPUB	2002/12
	Nicolation and the control of the co		US-PGPUB	2002/12
	$\mathbf{X}_{i}$		US-PGPUB	2002/12
	64440788.pn.		US-PGPUB	2002/12
			US-PGPUB US-PGPUB	2002/12
	( "4050965" "5552624"		US-PGPUB	2002/12
117 7	: 55525.4* (floating adj (gate or electrode)) and ((second adj drain) with (lower))		US-PGPUB	2002/12
118 1			US-PGPUB	2002/12
			US-PGPUB	2002/12
			US-PGPUB	2002/12
	(floating adj (gate or electrode)) and ((below or beneath or under) with (second adj drain) with ((first adj drain) or surface))		US-PGPUB	2002/12
	(floating adj (gate or electrode)) and (second adj drain) and (vertical with (non\$1volatile or eprom or eeprom or (non adj volatile)			2002/12
124 13	((floating ad) (gate or electrode)) and (pocket with drain)) and ((below or beneath or under) with (pocket) with (drain or surface))	USPAT	US-PGPUB	2002/12
125 0	((floating adj (gate or electrode)) and (pocket with drain)) and ((below or beneath or under) with (pocket) with ( drain or surface))	EPO: JF	O: DERWENT: IBM	2002/12
126 6	((floating adj (gate or electrode)) and (halo with drain)) and ((below or beneath or under) with (halo) with (drain or surface))		US-PGPUB	2002/12
			US-PGPUB	2002/12
128 1		USPAT		2002/12
129 1		USPAT		2002/12
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Hits		DBs	Time 8
111 7	(floating adj (gate or electrode)) and (*5349225*	USPAT; US-PGPUB	2002/12
1127	(non\$1volatile or (non adj volatile)) and (*5349225*	USPAT; US-PGPUB	2002/12
113 2	((non\$1volatile or (non adj volatile)) and ("5349225"	USPAT; US-PGPUB	2002/12/
114 0	64440788.pn.	USPAT; US-PGPUB	2002/12
115 1	6440788.pn.	USPAT; US-PGPUB	2002/12
116 17	( "4050965"	USPAT; US-PGPUB	2002/12
117 7	*5552624*	USPAT; US-PGPUB	2002/12
118 11	(floating adj (gate or electrode)) and ((second adj drain) with (lower))	USPAT; US-PGPUB	2002/12
119 1	(floating adj (gate or electrode)) and (sub\$1channel or (sub adj channel)) and (second adj drain)	USPAT; US-PGPUB	2002/12
120 9	(floating adj (gate or electrode)) and (doping adj channel ) and (second adj drain)	USPAT; US-PGPUB	2002/12
121 21	(floating adj (gate or electrode)) and ((below or beneath or under) with (second adj drain))	USPAT; US-PGPUB	2002/12
122 15	(floating adj (gate or electrode)) and ((below or beneath or under) with (second adj drain) with ((first adj drain) or surface))	USPAT; US-PGPUB	2002/12
123 14	(floating adj (gate or electrode)) and (second adj drain) and (vertical with (non\$1volatile or eprom or eeprom or (non adj volatile)	USPAT; US-PGPUB	2002/12
124 13	((floating adj (gate or electrode)) and (pocket with drain)) and ((below or beneath or under) with (pocket) with ( drain or surface))	USPAT; US-PGPUB	2002/12
125 0	((floating adj (gate or electrode)) and (pocket with drain)) and ((below or beneath or under) with (pocket) with ( drain or surface))	EPO; JPO; DERWENT; IBM_	2002/12
128 6	((floating adj (gate or electrode)) and (halo with drain)) and ((below or beneath or under) with (halo) with ( drain or surface))	USPAT; US-PGPUB	2002/12
127 3	((floating adj (gate or electrode)) and (halo with drain)) and ((below or beneath or under) adj drain)	USPAT; US-PGPUB	2002/12
128 1	*4868619*.PN.	USPAT	2002/12
129 1	*4939558*.PN.	USPAT	2002/12
130 1	*5422506*.PN.	USPAT	2002/12
131 1	*5548143*.PN.	USPAT	2002/12
132 12	<b>"6340377"</b>	JPO; DERWENT	2002/12
133 7	<b>"6340377"</b>	DERWENT	2002/12
134 5	*6340377 <b>*</b>	JPO	2002/12
135 2	<b>"6048770"</b>	USPAT; US-PGPUB	2002/12
136 12	*5691560*	USPAT; US-PGPUB	2002/12
137 4	(floating adj (gate or electrode)) and "5780902"	USPAT; US-PGPUB	2002/12
138 6	(floating adj (gate or electrode)) and "5691560"	USPAT; US-PGPUB	2002/12
138 20	(floating adj (gate or electrode)) and (region adj (below or beneath or under) adj drain)	USPAT; US-PGPUB	2002/12
140 9	("6278154"	USPAT; US-PGPUB	2002/12
141 4	((floating adj (gate or electrode)) and (pocket with drain)) and ((below or beneath or under) adj drain)	USPAT; US-PGPUB	2002/12
142 8	(( "6278154"	USPAT; US-PGPUB	2002/12
143 2	(SUGIYAMA and ODANAKA and FUJIMOTO and OGURA).in.	USPAT; US-PGPUB	2002/12
144 21	*4665418*	USPAT; US-PGPUB	2002/12
145 5	(drain with (electric\$1 field or (electric adj field))) and (floating adj (gate or electrode)) and ((257/314.ccls.) or (257/315.ccls.)) an	USPAT; US-PGPUB	2002/12
	*5264384*	USPAT; US-PGPUB	2002/12
	("5646430"	USPAT; US-PGPUB	2002/12
	<u>"5646430"</u>	USPAT; US-PGPUB	2002/12
149 2	"5646430"	EPO; DERWENT	2002/12
	*11345888*	JPO; DERWENT	2002/12
151 8	(hori and kato and odanaka).in.	USPAT; US-PGPUB	2002/12
	((hori and kato and odanaka) in.) not ((atsushi and junichi and shinji) in.)	USPAT; US-PGPUB	2002/12
153 14	(hori and kato and odanaka).in.	EPO; JPO; DERWENT; IBM_	2002/12
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